



YJD25GP06A

P-Channel Enhancement Mode Field Effect Transistor

Product Summary

V_{DS}	-60V
I_{D25}	



Typical Performance Characteristics

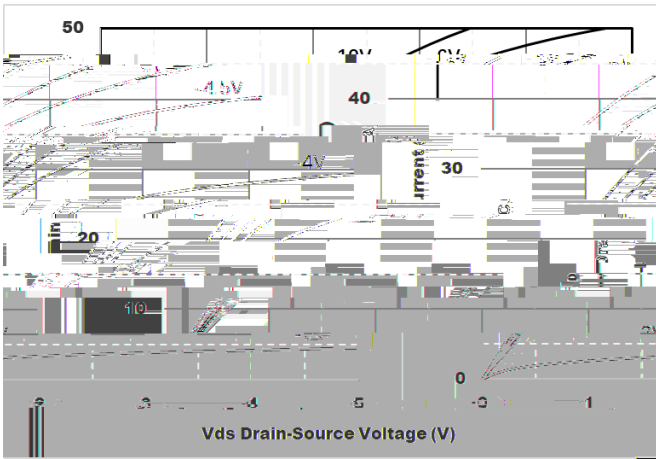


Figure1. Output Characteristics

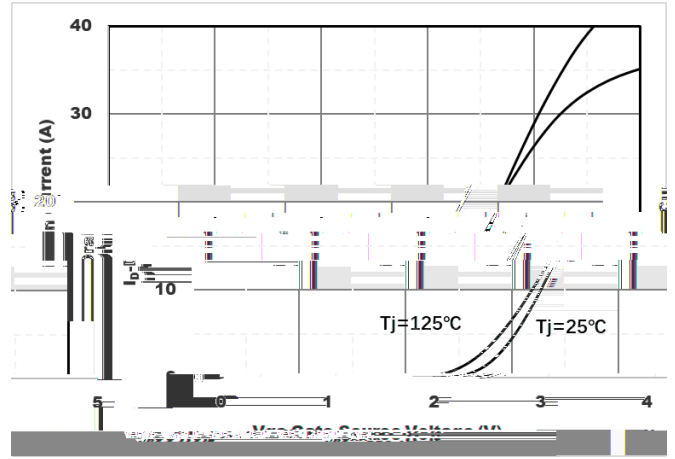


Figure2. Transfer Characteristics

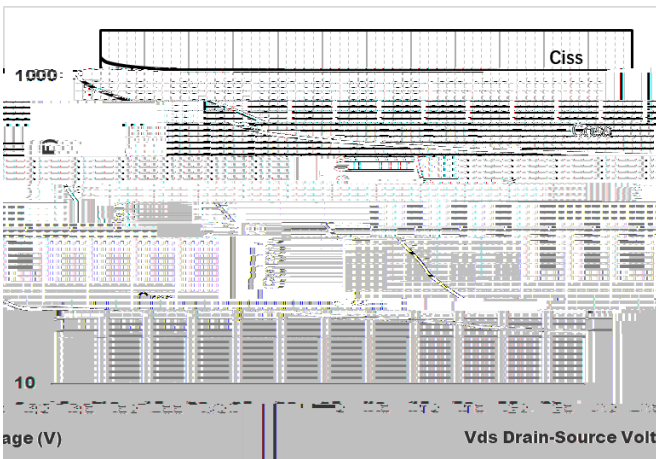


Figure3. Capacitance Characteristics

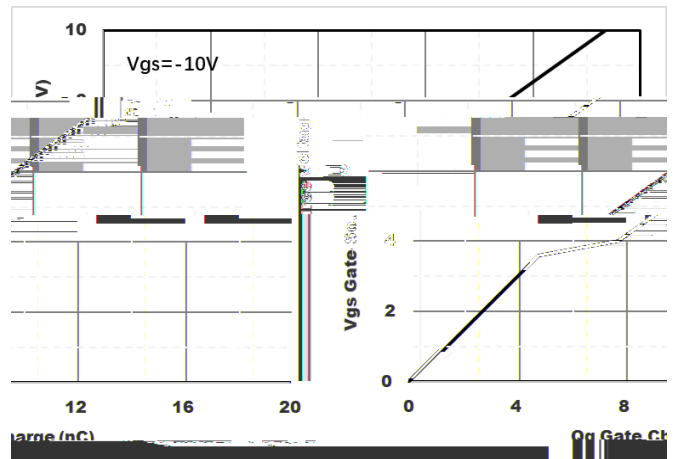


Figure4. Gate Charge

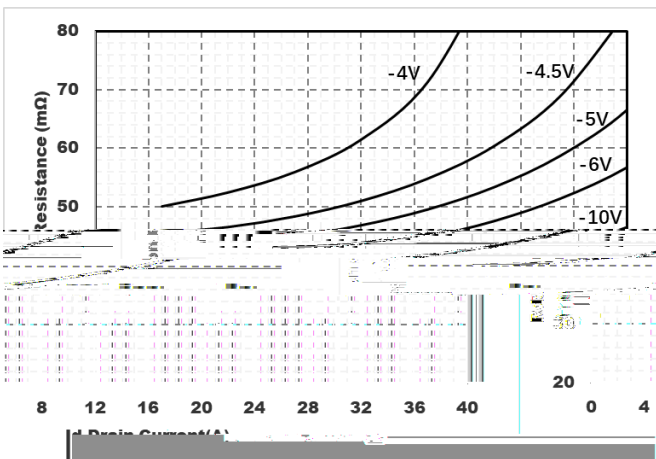


Figure5. : On-Resistance vs. Drain Current

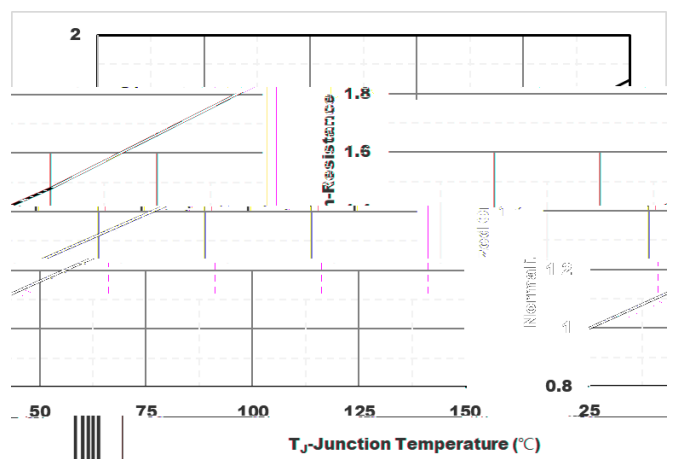


Figure6. Normalized On-Resistance



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Figure 7. Normalized Gate Threshold Voltage

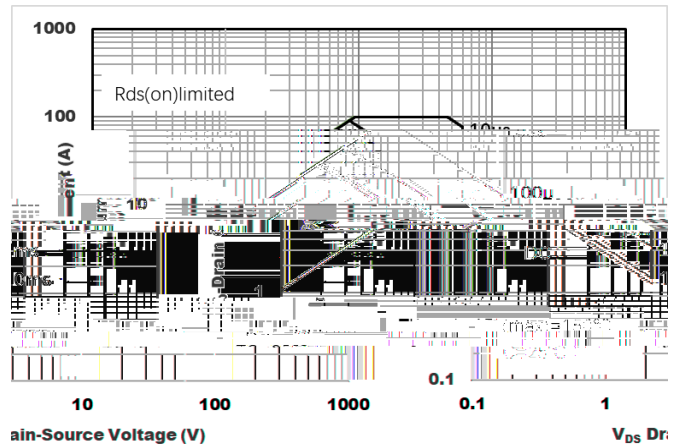


Figure 8. Safe Operation Area

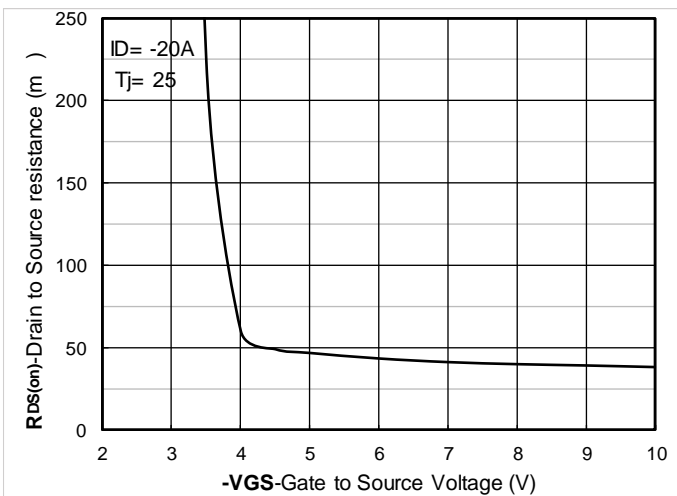


Figure 9. On-Resistance vs Gate to Source Voltage



Figure 10. Forward characteristics of reverse diode

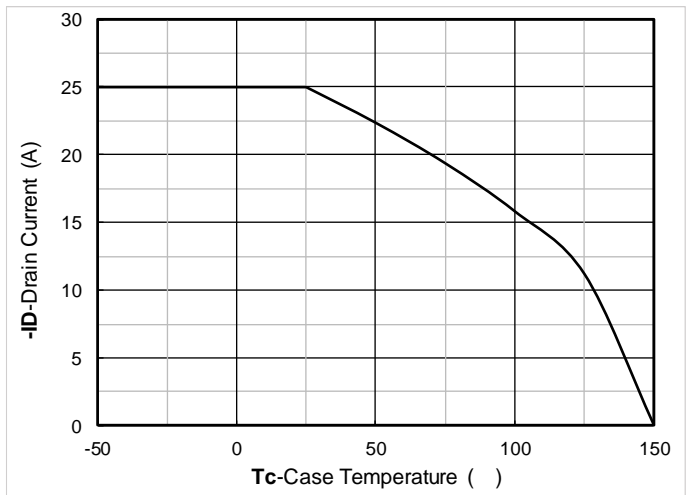


Figure 11. Normalized breakdown voltage

Figure 12. Current dissipation

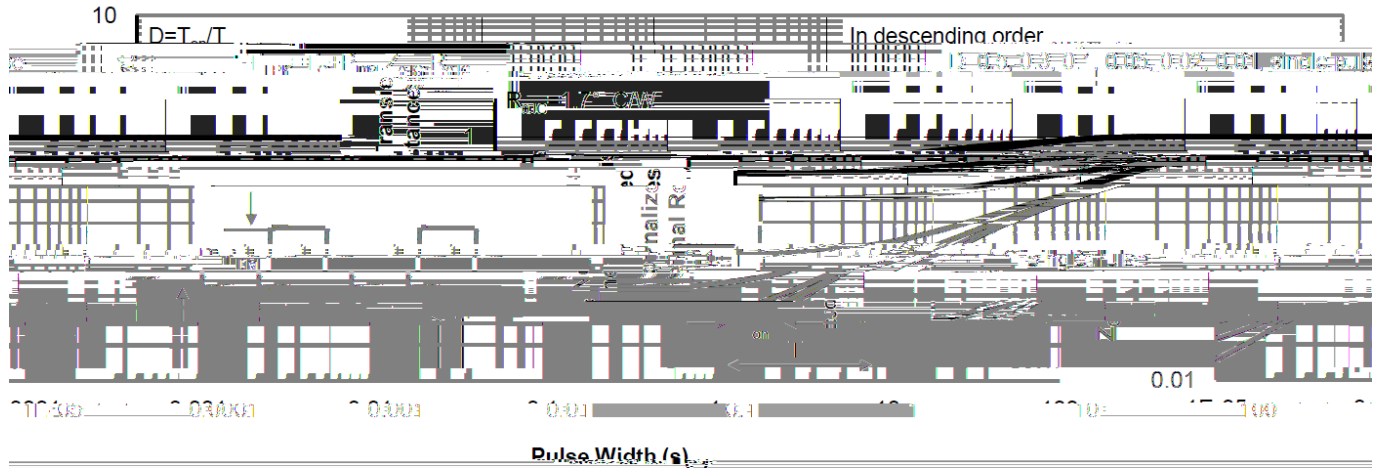
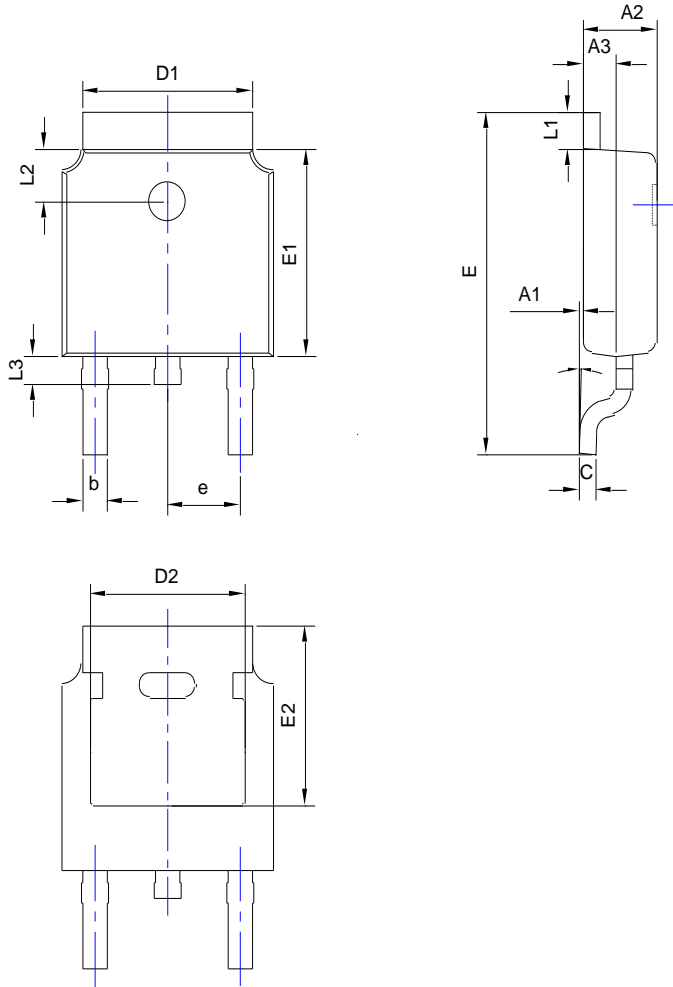


Figure13.Normalized Maximum Transient thermal impedance



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TO-252-B Package information



SYMBOL	DIMENSIONS		
	INCHES		
	MIN.	NOM.	
A1	0.000		
A2	0.087	0.091	
A3	0.035	0.039	
b	0.026	0.030	
c	0.018	0.020	
D	0.256	0.260	
D1			
D2	0.181	0.189	
E	0.390	0.398	
E1	0.236	0.240	

NOTE:
 1.PACKAGE BODY SIZES EXCLUDE MOLD FLASH AND GATE BURRS.
 2.TOLERANCE 0.1mm UNLESS OTHERWISE SPECIFIED.
 3.THE PAD LAYOUT IS FOR REFERENCE PURPOSES ONLY.

